

## CDx4HC(T)541 具有三态输出的高速 CMOS 逻辑八路缓冲器和线路驱动器

### 1 特性

- HC540、CD74HCT540：反相
- ' HC541、' HCT541：同相
- 缓冲输入
- 三态输出
- 总线驱动能力
- $V_{CC} = 5V$ 、 $C_L = 15pF$  且  $T_A = 25^\circ C$  时的传播延迟典型值为 9ns
- 扇出（在温度范围内）
  - 标准输出：10 个 LSTTL 负载
  - 总线驱动器输出：15 个 LSTTL 负载
- 宽工作温度范围： $-55^\circ C$  至  $125^\circ C$
- 平衡的传播延迟及转换时间
- 与 LSTTL 逻辑 IC 相比，可显著降低功耗
- HC 类型
  - 工作电压为 2V 至 6V
  - 高抗噪性：当  $V_{CC} = 5V$  时， $N_{IL} = 30\%$ ， $N_{IH} = V_{CC}$  的 30%
- HCT 类型
  - 工作电压为 4.5V 至 5.5V
  - 直接 LSTTL 输入逻辑兼容性， $V_{IL} = 0.8V$ （最大值）， $V_{IH} = 2V$ （最小值）
  - CMOS 输入兼容性，当电压为  $V_{OL}$ 、 $V_{OH}$  时， $I_I \leq 1\mu A$

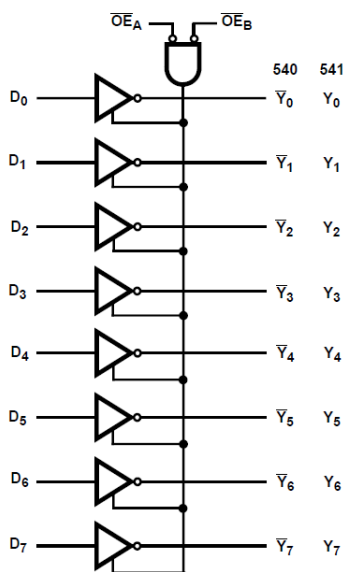
### 2 说明

' HC540 和 CD74HCT540 是具有三态输出的反相八路缓冲器和线路驱动器，能够驱动 15 个 LSTTL 负载。' HC541 和 ' HCT541 是具有三态输出的同相八路缓冲器和线路驱动器，能够驱动 15 个 LSTTL 负载。输出使能 ( $\overline{OE1}$ ) 和 ( $\overline{OE2}$ ) 控制三态输出。如果  $\overline{OE1}$  或  $\overline{OE2}$  为高电平，则输出处于高阻抗状态。对于数据输出， $\overline{OE1}$  和  $\overline{OE2}$  都必须为低电平。

#### 器件信息

器件型号	封装 <sup>(1)</sup>	封装尺寸 (标称值)
CD74HC540M	SOIC (20)	12.80mm × 7.50mm
CD74HC540E	PDIP (20)	25.40mm × 6.35mm
CD54HC540F3A	CDIP (20)	26.92mm × 6.92mm
CD74HC541M	SOIC (20)	12.80mm × 7.50mm
CD74HC541E	PDIP (20)	25.40mm × 6.35mm
CD54HC541F	CDIP (20)	26.92mm × 6.92mm
CD74HCT540M	SOIC (20)	12.80mm × 7.50mm
CD74HCT540E	PDIP (20)	25.40mm × 6.35mm
CD74HCT541M	SOIC (20)	12.80mm × 7.50mm
CD74HCT541E	PDIP (20)	25.40mm × 6.35mm
CD54HCT541F	CDIP (20)	26.92mm × 6.92mm
CD74HCT541PW	TSSOP (20)	6.50mm × 4.40mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



功能图



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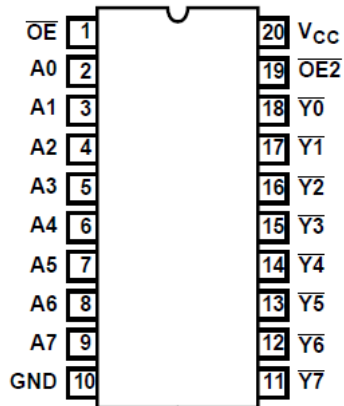
### 3 Revision History

注：以前版本的页码可能与当前版本的页码不同

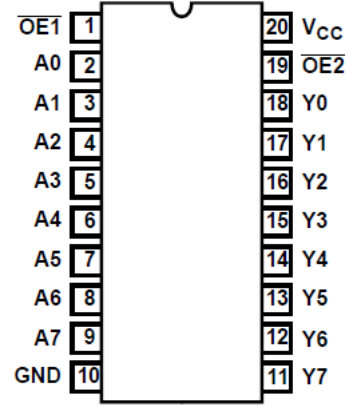
<b>Changes from Revision C (July 2004) to Revision D (January 2022)</b>	<b>Page</b>
• 更新了整个文档中的编号、格式、表格、图和交叉参考，以反映现代数据表标准.....	1



## 4 Pin Configuration and Functions



**HC540**  
J, N, or DW package  
20-Pin CDIP, PDIP, or SOIC  
Top View



**HC541**  
J, N, DW, or PW  
20-Pin CDIP, PDIP, SOIC, or TSSOP  
Top View

## 5 Specifications

### 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage	- 0.5	7	V
I <sub>IK</sub>	Input diode current	For V <sub>I</sub> < - 0.5 V or V <sub>I</sub> > V <sub>CC</sub> + 0.5 V		±20 mA
I <sub>OK</sub>	Output diode current	For V <sub>O</sub> < - 0.5 V or V <sub>O</sub> > V <sub>CC</sub> + 0.5 V		±20 mA
I <sub>O</sub>	Drain current, per output	For - 0.5 V < V <sub>O</sub> < V <sub>CC</sub> + 0.5 V		±35 mA
I <sub>O</sub>	Output source or sink current per output pin	For V <sub>O</sub> > - 0.5 V or V <sub>O</sub> < V <sub>CC</sub> + 0.5 V		±25 mA
Continuous current through V <sub>CC</sub> or ground current				±50 mA
T <sub>J</sub>	Junction temperature			150 °C
T <sub>stg</sub>	Storage temperature range	- 65	150	°C
Lead temperature (Soldering 10s) (SOIC - Lead Tips Only)				300 °C

- (1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If briefly operating outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.

### 5.2 Recommended Operating Conditions

		MIN	MAX	UNIT
T <sub>A</sub>	Temperature range	- 55	125	°C
V <sub>CC</sub>	Supply voltage range	HC types	6	V
		HCT types	4.5	
V <sub>I</sub> , V <sub>O</sub>	Input or output voltage	0	V <sub>CC</sub>	V
	Input rise and fall time	2 V	1000	ns
		4.5 V	500	
		6 V	400	

### 5.3 Thermal Information

THERMAL METRIC		DW (SOIC)	N (PDIP)	PW (TSSOP)	UNIT
		20 PINS	20 PINS	20 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance <sup>(1)</sup>	58	69	83	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics](#) application report.

## 5.4 Electrical Characteristics

PARAMETER		TEST CONDITIONS <sup>(2)</sup>	V <sub>CC</sub> (V)	25°C			-40°C to 85°C		-55°C to 125°C		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
<b>HC TYPES</b>											
V <sub>IH</sub>	High level input voltage		2	1.5			1.5		1.5		V
			4.5	3.15			3.15		3.15		
			6	4.2			4.2		4.2		
V <sub>IL</sub>	Low level input voltage		2	0.5			0.5		0.5		V
			4.5	1.35			1.35		1.35		
			6	1.8			1.8		1.8		
V <sub>OH</sub>	High level output voltage CMOS loads	I <sub>OH</sub> = -20 μA	2	1.9			1.9		1.9		V
		I <sub>OH</sub> = -20 μA	4.5	4.4			4.4		4.4		
		I <sub>OH</sub> = -20 μA	6	5.9			5.9		5.9		
	High level output voltage TTL loads	I <sub>OH</sub> = -6 mA	4.5	3.98			3.84		3.7		
I <sub>OH</sub> = -7.8 mA		6	5.48			5.34		5.2			
V <sub>OL</sub>	Low level output voltage CMOS loads	I <sub>OL</sub> = 20 μA	2	0.1			0.1		0.1		V
		I <sub>OL</sub> = 20 μA	4.5	0.1			0.1		0.1		
		I <sub>OL</sub> = 20 μA	6	0.1			0.1		0.1		
	Low level output voltage TTL loads	I <sub>OL</sub> = 6 mA	4.5	0.26			0.33		0.4		
I <sub>OL</sub> = 7.8 mA		6	0.26			0.33		0.4			
I <sub>I</sub>	Input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND	6	±0.1			±1		±1		μA
I <sub>CC</sub>	Quiescent device current	V <sub>I</sub> = V <sub>CC</sub> or GND	6	8			80		160		μA
I <sub>OZ</sub>	Three-state leakage current	V <sub>O</sub> = V <sub>CC</sub> or GND	6	±0.5			±5.0		±10		μA
<b>HCT TYPES</b>											
V <sub>IH</sub>	High level input voltage		4.5 to 5.5	2			2		2		V
V <sub>IL</sub>	Low level input voltage		4.5 to 5.5	0.8			0.8		0.8		V
V <sub>OH</sub>	High level output voltage CMOS loads	V <sub>OH</sub> = -20 μA	4.5	4.4			4.4		4.4		V
	High level output voltage TTL loads	V <sub>OH</sub> = -6 mA	4.5	3.98			3.84		3.7		
V <sub>OL</sub>	Low level output voltage CMOS loads	V <sub>OL</sub> = 20 μA	4.5	0.1			0.1		0.1		V
	Low level output voltage TTL loads	V <sub>OL</sub> = 6 mA	4.5	0.26			0.33		0.4		
I <sub>I</sub>	Input leakage current	V <sub>I</sub> = V <sub>CC</sub> and GND	5.5	±0.1			±1		±1		μA
I <sub>CC</sub>	Quiescent device current	V <sub>I</sub> = V <sub>CC</sub> and GND	5.5	8			80		160		μA
I <sub>OZ</sub>	Three-state leakage current	V <sub>O</sub> = V <sub>CC</sub> or GND	5.5	±0.5			±5.0		±10		μA

## 5.4 Electrical Characteristics (continued)

PARAMETER		TEST CONDITIONS <sup>(2)</sup>	V <sub>CC</sub> (V)	25°C			- 40°C to 85°C		- 55°C to 125°C		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Δ I <sub>CC</sub> <sup>(1)</sup>	HCT540 Additional quiescent device current per input pin	A0 - A7 inputs held at V <sub>CC</sub> - 2.1	4.5 to 5.5		100	360		450		490	μ A
		$\overline{OE}2$ input held at V <sub>CC</sub> - 2.1	4.5 to 5.5		100	270		337.5		367.5	μ A
		$\overline{OE}1$ input held at V <sub>CC</sub> - 2.1	4.5 to 5.5		100	414		517.5		563.5	μ A
	HCT541 Additional quiescent device current per input pin	A0 - A7 inputs held at V <sub>CC</sub> - 2.1	4.5 to 5.5		100	144		180		196	μ A
		$\overline{OE}2$ input held at V <sub>CC</sub> - 2.1	4.5 to 5.5		100	270		337.5		367.5	μ A
		$\overline{OE}1$ input held at V <sub>CC</sub> - 2.1	4.5 to 5.5		100	414		517.5		563.5	μ A

(1) For dual-supply systems theoretical worst case (V<sub>I</sub> = 2.4 V, V<sub>CC</sub> = 5.5 V) specification is 1.8mA.

(2) V<sub>I</sub> = V<sub>IH</sub> or V<sub>OL</sub>, unless otherwise noted.

## 5.5 Switching Characteristics

PARAMETER		TEST CONDITIONS	V <sub>CC</sub> (V)	25°C			- 40°C to 85°C		- 55°C to 125°C		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
<b>HC TYPES</b>											
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation delay Data to outputs (540)	C <sub>L</sub> = 50 pF	2			110		140		165	ns
			4.5			22		28	33		
		C <sub>L</sub> = 15 pF	5		9						ns
			6			19		24	28		
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Data to outputs (541)	C <sub>L</sub> = 50 pF	2			115		145		175	ns
			4.5			23		29	35		
		C <sub>L</sub> = 15 pF	5		9						ns
			6			20		25	30		
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Output enable and disable to outputs (540)	C <sub>L</sub> = 50 pF	2			160		200		240	ns
			4.5			32		40	48		
		C <sub>L</sub> = 15 pF	5		13						ns
			6			27		34	41		
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Output enable and disable to outputs (541)	C <sub>L</sub> = 50 pF	2			160		200		240	ns
			4.5			32		40	48		
		C <sub>L</sub> = 15 pF	5		14						ns
			6			23		29	35		
t <sub>THL</sub> , t <sub>TLH</sub>	Output transition time	C <sub>L</sub> = 50 pF	2			60		75		90	ns
			4.5			12		15	18		
			6			10		13	15		
C <sub>I</sub>	Input capacitance	C <sub>L</sub> = 50 pF		10	10		10	10		pF	
C <sub>O</sub>	Three-state output capacitance			20	20		20	20		pF	
C <sub>PD</sub>	Power dissipation capacitance <sup>(1) (2)</sup> (540)	C <sub>L</sub> = 15 pF	5	50						pF	
C <sub>PD</sub>	Power dissipation capacitance <sup>(1) (2)</sup> (541)	C <sub>L</sub> = 15 pF	5	48						pF	
<b>HCT TYPES</b>											

## 5.5 Switching Characteristics (continued)

PARAMETER		TEST CONDITIONS	V <sub>CC</sub> (V)	25°C			- 40°C to 85°C		- 55°C to 125°C		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t <sub>PHL</sub> , t <sub>PLH</sub>	Propagation delay Data to outputs (540)	C <sub>L</sub> = 50 pF	4.5		24		30		36	ns	
		C <sub>L</sub> = 15 pF	5	9							
t <sub>PHL</sub> , t <sub>PLH</sub>	Data to outputs (541)	C <sub>L</sub> = 50 pF	4.5		28		35		42	ns	
		C <sub>L</sub> = 15 pF	5	11							
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Output enable and disable to outputs (540, 541)	C <sub>L</sub> = 50 pF	4.5		35		44		53	ns	
		C <sub>L</sub> = 15 pF	5	14							
t <sub>TLH</sub> , t <sub>THL</sub>	Output transition time	C <sub>L</sub> = 50 pF	4.5		12		15		18	ns	
C <sub>I</sub>	Input capacitance	C <sub>L</sub> = 50 pF		10	10		10		10	pF	
C <sub>O</sub>	Three-state output capacitance			20	20		20		20	pF	
C <sub>PD</sub>	Power dissipation capacitance <sup>(1) (2)</sup> (540, 541)	C <sub>L</sub> = 15 pF	5	55						pF	

(1) C<sub>PD</sub> is used to determine the dynamic power consumption, per channel.

(2) P<sub>D</sub> = V<sub>CC</sub><sup>2</sup>f<sub>i</sub>(C<sub>PD</sub> + C<sub>L</sub>) where f<sub>i</sub> = input frequency, C<sub>L</sub> = output load capacitance, V<sub>CC</sub> = supply voltage.

## 6 Parameter Measurement Information

$t_{pd}$  is the maximum between  $t_{PLH}$  and  $t_{PHL}$

$t_t$  is the maximum between  $t_{TLH}$  and  $t_{THL}$

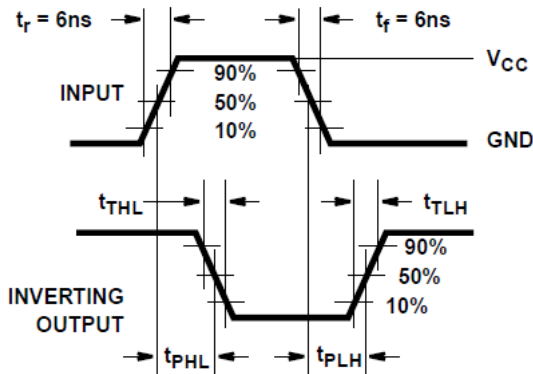


图 6-1. HC Transition Times and Propagation Delay Times, Combination Logic

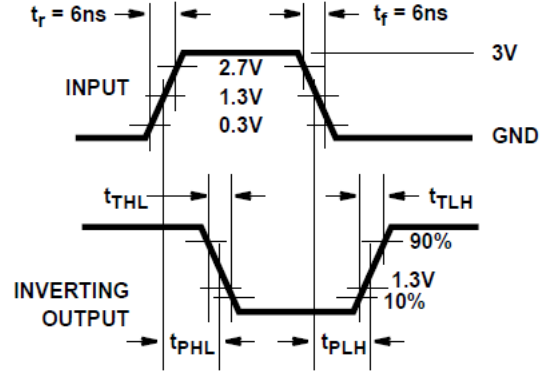


图 6-2. HCT Transition Times and Propagation Delay Times, combination Logic

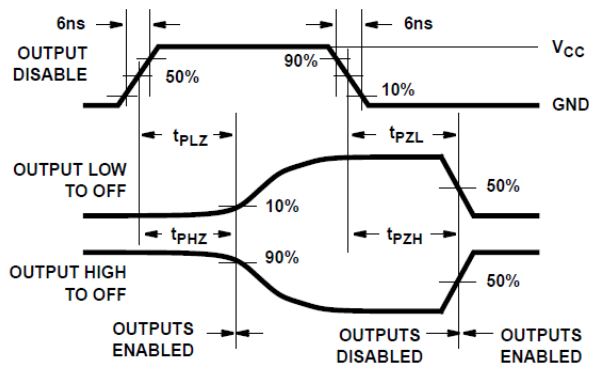


图 6-3. HC Three-State Propagation Delay Waveform

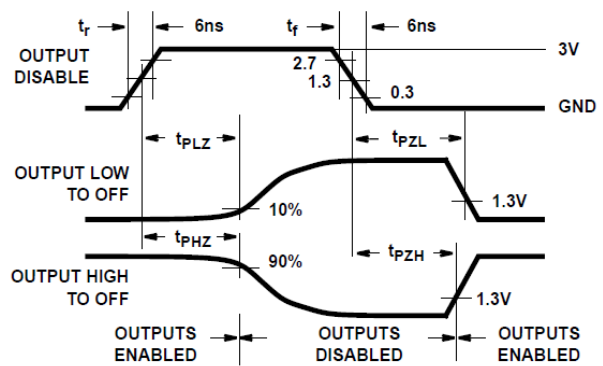
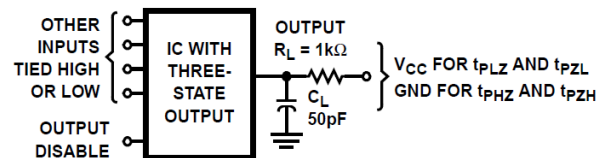


图 6-4. HCT Three-State Propagation Delay Waveform



- A. Open drain waveforms  $t_{PLZ}$  and  $t_{PZL}$  are the same as those for three-state shown on the left. The test circuit is Output  $R_L = 1k\Omega$  to  $V_{CC}$ ,  $C_L = 50pF$ .

图 6-5. HC and HCT Three-State Propagation Delay Test Circuit

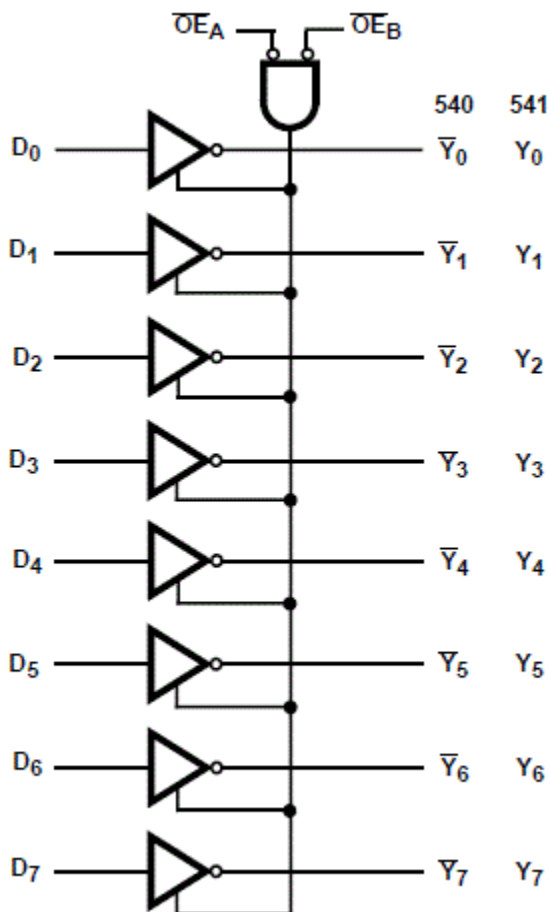


## 7 Detailed Description

### 7.1 Overview

The ' HC540 and CD74HCT540 are Inverting Octal Buffers and Line Drivers with Three-State Outputs and the capability to drive 15 LSTTL loads. The ' HC541 and ' HCT541 are Noninverting Octal Buffers and Line Drivers with Three-State Outputs that can drive 15 LSTTL loads. The Output Enables ( $\overline{OE1}$ ) and ( $\overline{OE2}$ ) control the Three-State Outputs. If either  $\overline{OE1}$  or  $\overline{OE2}$  is HIGH the outputs will be in the high impedance state. For data output  $\overline{OE1}$  and  $\overline{OE2}$  both must be LOW.

### 7.2 Functional Block Diagram



### 7.3 Device Functional Modes

表 7-1. Truth Table<sup>(1)</sup>

INPUTS			OUTPUTS	
$\overline{OE1}$	$\overline{OE2}$	$A_n$	540	541
L	L	H	L	H
H	X	X	Z	Z
X	H	X	Z	Z
L	L	L	H	L

(1) H = high voltage level, L = low voltage level, X = don't care, Z = high impedance

## 8 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- $\mu$ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- $\mu$ F and 1- $\mu$ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

## 9 Layout

### 9.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or  $V_{CC}$ , whichever makes more sense for the logic function or is more convenient.

## 10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

### 10.1 接收文档更新通知

要接收文档更新通知，请导航至 [ti.com](http://ti.com) 上的器件产品文件夹。点击 [订阅更新](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

### 10.2 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

### 10.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

所有商标均为其各自所有者的财产。

### 10.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 10.5 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CD54HC540F3A	ACTIVE	CDIP	J	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	CD54HC540F3A	<a href="#">Samples</a>
CD54HC541F	ACTIVE	CDIP	J	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	CD54HC541F	<a href="#">Samples</a>
CD54HC541F3A	ACTIVE	CDIP	J	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	CD54HC541F3A	<a href="#">Samples</a>
CD54HCT541F	ACTIVE	CDIP	J	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	CD54HCT541F	<a href="#">Samples</a>
CD54HCT541F3A	ACTIVE	CDIP	J	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	CD54HCT541F3A	<a href="#">Samples</a>
CD74HC540E	ACTIVE	PDIP	N	20	20	RoHS & Non-Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC540E	<a href="#">Samples</a>
CD74HC540M	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC540M	<a href="#">Samples</a>
CD74HC540M96	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC540M	<a href="#">Samples</a>
CD74HC541E	ACTIVE	PDIP	N	20	20	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC541E	<a href="#">Samples</a>
CD74HC541EE4	ACTIVE	PDIP	N	20	20	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC541E	<a href="#">Samples</a>
CD74HC541M	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC541M	<a href="#">Samples</a>
CD74HC541M96	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC541M	<a href="#">Samples</a>
CD74HC541M96G4	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC541M	<a href="#">Samples</a>
CD74HC541PW	ACTIVE	TSSOP	PW	20	70	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HJ541	<a href="#">Samples</a>
CD74HC541PWR	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HJ541	<a href="#">Samples</a>
CD74HCT540E	ACTIVE	PDIP	N	20	20	RoHS & Non-Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT540E	<a href="#">Samples</a>
CD74HCT540M	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT540M	<a href="#">Samples</a>
CD74HCT540M96	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT540M	<a href="#">Samples</a>

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CD74HCT541E	ACTIVE	PDIP	N	20	20	RoHS & Non-Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT541E	<a href="#">Samples</a>
CD74HCT541M	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT541M	<a href="#">Samples</a>
CD74HCT541M96	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT541M	<a href="#">Samples</a>
CD74HCT541M96E4	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT541M	<a href="#">Samples</a>
CD74HCT541M96G4	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT541M	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSELETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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**OTHER QUALIFIED VERSIONS OF CD54HC540, CD54HC541, CD54HCT541, CD74HC540, CD74HC541, CD74HCT541 :**

- Catalog : [CD74HC540](#), [CD74HC541](#), [CD74HCT541](#)
- Military : [CD54HC540](#), [CD54HC541](#), [CD54HCT541](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product
- Military - QML certified for Military and Defense Applications

**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD74HC540M96	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
CD74HC541M96	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
CD74HC541M96	SOIC	DW	20	2000	330.0	24.4	10.9	13.3	2.7	12.0	24.0	Q1
CD74HC541PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
CD74HC541PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
CD74HCT540M96	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
CD74HCT541M96	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1



**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CD74HC540M96	SOIC	DW	20	2000	367.0	367.0	45.0
CD74HC541M96	SOIC	DW	20	2000	367.0	367.0	45.0
CD74HC541M96	SOIC	DW	20	2000	367.0	367.0	45.0
CD74HC541PWR	TSSOP	PW	20	2000	356.0	356.0	35.0
CD74HC541PWR	TSSOP	PW	20	2000	356.0	356.0	35.0
CD74HCT540M96	SOIC	DW	20	2000	367.0	367.0	45.0
CD74HCT541M96	SOIC	DW	20	2000	367.0	367.0	45.0

**TUBE**


\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
CD74HC540E	N	PDIP	20	20	506	13.97	11230	4.32
CD74HC540M	DW	SOIC	20	25	507	12.83	5080	6.6
CD74HC541E	N	PDIP	20	20	506	13.97	11230	4.32
CD74HC541EE4	N	PDIP	20	20	506	13.97	11230	4.32
CD74HC541M	DW	SOIC	20	25	507	12.83	5080	6.6
CD74HC541PW	PW	TSSOP	20	70	530	10.2	3600	3.5
CD74HCT540E	N	PDIP	20	20	506	13.97	11230	4.32
CD74HCT540M	DW	SOIC	20	25	507	12.83	5080	6.6
CD74HCT541E	N	PDIP	20	20	506	13.97	11230	4.32
CD74HCT541M	DW	SOIC	20	25	507	12.83	5080	6.6

# PW0020A



# PACKAGE OUTLINE

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



### NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

# EXAMPLE BOARD LAYOUT

PW0020A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE: 10X



SOLDER MASK DETAILS

4220206/A 02/2017

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

PW0020A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE: 10X

4220206/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Publication IPC-7351 is recommended for alternate design.
  - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
  - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

J (R-GDIP-T\*\*)

14 LEADS SHOWN

CERAMIC DUAL IN-LINE PACKAGE



DIM \ PINS **	14	16	18	20
A	0.300 (7,62) BSC	0.300 (7,62) BSC	0.300 (7,62) BSC	0.300 (7,62) BSC
B MAX	0.785 (19,94)	.840 (21,34)	0.960 (24,38)	1.060 (26,92)
B MIN	—	—	—	—
C MAX	0.300 (7,62)	0.300 (7,62)	0.310 (7,87)	0.300 (7,62)
C MIN	0.245 (6,22)	0.245 (6,22)	0.220 (5,59)	0.245 (6,22)



4040083/F 03/03

- NOTES:
- All linear dimensions are in inches (millimeters).
  - This drawing is subject to change without notice.
  - This package is hermetically sealed with a ceramic lid using glass frit.
  - Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
  - Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

N (R-PDIP-T\*\*)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- NOTES:
- A. All linear dimensions are in inches (millimeters).
  - B. This drawing is subject to change without notice.
  - C Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
  - D The 20 pin end lead shoulder width is a vendor option, either half or full width.



# DW0020A



# PACKAGE OUTLINE

## SOIC - 2.65 mm max height

SOIC



### NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
5. Reference JEDEC registration MS-013.

# EXAMPLE BOARD LAYOUT

DW0020A

SOIC - 2.65 mm max height

SOIC



LAND PATTERN EXAMPLE  
SCALE:6X



SOLDER MASK DETAILS

4220724/A 05/2016

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DW0020A

SOIC - 2.65 mm max height

SOIC



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:6X

4220724/A 05/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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